

isc N-Channel MOSFET Transistor

2SK783

FEATURES

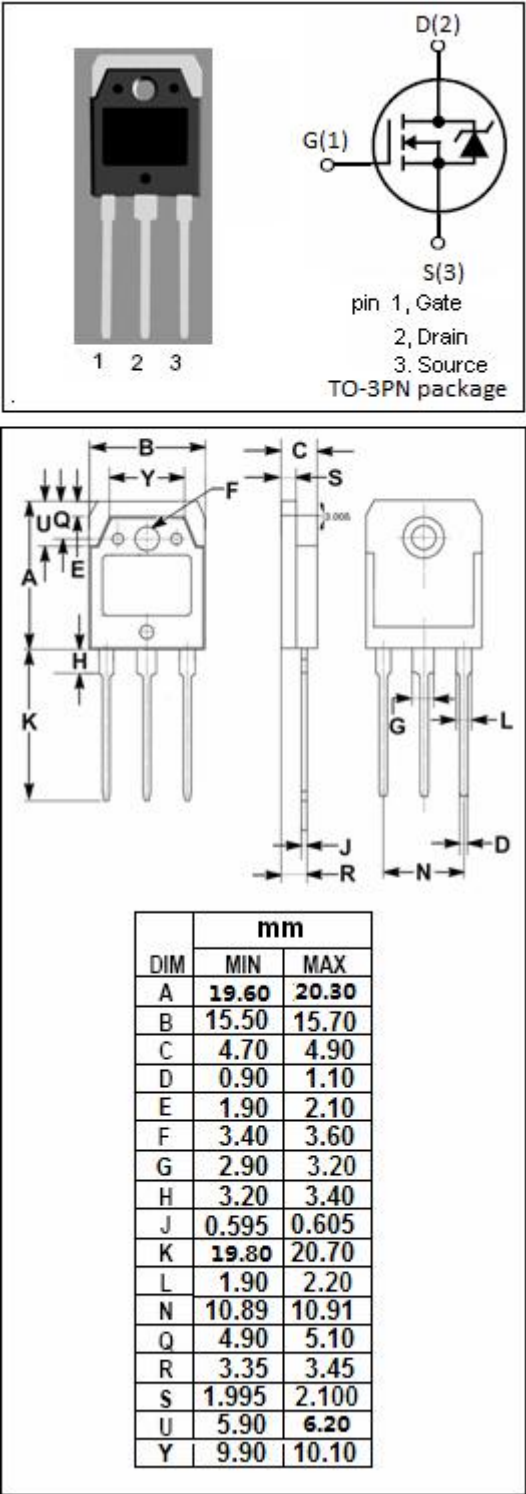
- Drain Current $-I_D=12A@T_C=25^{\circ}C$
- Drain Source Voltage-
: $V_{DSS}=500V(\text{Min})$
- Fast Switching Speed

DESCRIPTION

- Designed especially for high voltage,high speed applications, such as switching power supplies .

ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage	500	V
V_{GS}	Gate-Source Voltage-Continuous	± 20	V
I_D	Drain Current-Continuous	12	A
P_D	Total Dissipation @ $T_C=25^{\circ}C$	125	W
T_J	Max. Operating Junction Temperature	150	$^{\circ}C$
T_{stg}	Storage Temperature	-55~150	$^{\circ}C$



isc N-Channel MOSFET Transistor**2SK783****ELECTRICAL CHARACTERISTICS** $T_c=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0$; $I_D=0.25\text{mA}$	500			V
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$; $I_D=1\text{mA}$	2.1		4.0	V
$R_{DS(on)}$	Drain-Source On-Resistance	$V_{GS}=10\text{V}$; $I_D=6\text{A}$			0.57	Ω
I_{GSS}	Gate-Body Leakage Current	$V_{GS}=\pm 20\text{V}$; $V_{DS}=0$			± 100	nA
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=500\text{V}$; $V_{GS}=0$			500	μA
V_{SD}	Forward On-Voltage	$I_S=12\text{A}$; $V_{GS}=0$		1.2		V